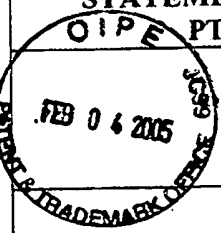


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AKS	5,561,681	October 1, 1996	Nishimura TAKASHI			
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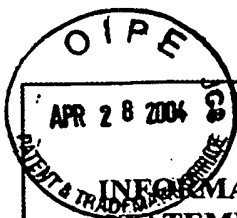
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						YES	NO
AKS	1 139 526	October 4, 2001	EP			English Document	

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	APPLICANT(S) Susumu KONDO et al.	
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AKS	9-214045	August 15, 1997	Japan			X	
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